

2SC3757

Silicon NPN epitaxial planar type

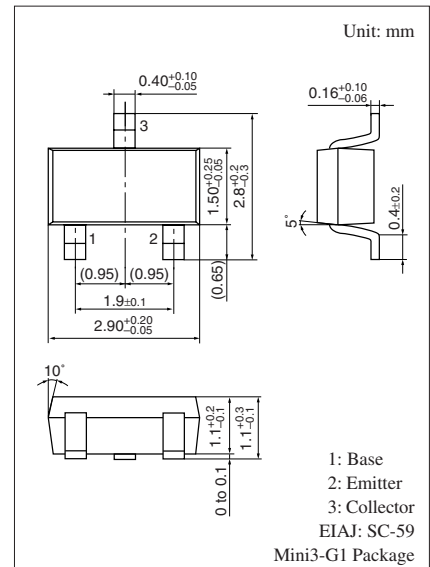
For high-speed switching

■ Features

- Low collector-emitter saturation voltage $V_{CE(sat)}$
- Mini type package, allowing downsizing of the equipment and automatic insertion through the tape packing and the magazine packing

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	V_{CBO}	40	V
Collector-emitter voltage (E-B short)	V_{CES}	40	V
Emitter-base voltage (Collector open)	V_{EBO}	5	V
Collector current	I_C	100	mA
Peak collector current	I_{CP}	300	mA
Collector power dissipation	P_C	200	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$



Marking Symbol: 2Y

■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = 15\text{ V}, I_E = 0$			0.1	μA
Emitter-base cutoff current (Collector open)	I_{EBO}	$V_{EB} = 4\text{ V}, I_C = 0$			0.1	μA
Forward current transfer ratio *	h_{FE}	$V_{CE} = 1\text{ V}, I_C = 10\text{ mA}$	60		200	—
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 10\text{ mA}, I_B = 1\text{ mA}$		0.17	0.25	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = 10\text{ mA}, I_B = 1\text{ mA}$			1.0	V
Transition frequency	f_T	$V_{CB} = 10\text{ V}, I_E = -10\text{ mA}, f = 200\text{ MHz}$		450		MHz
Collector output capacitance (Common base, input open circuited)	C_{ob}	$V_{CB} = 10\text{ V}, I_E = 0, f = 1\text{ MHz}$		2	6	pF
Turn-on time	t_{on}	Refer to the switching time measurement circuit		17		ns
Turn-off time	t_{off}			17		ns
Storage time	t_{stg}			10		ns

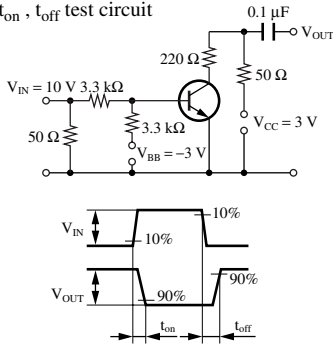
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. *: Rank classification

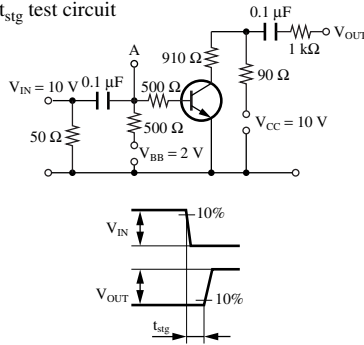
Rank	Q	R
h_{FE}	60 to 120	90 to 200

Switching time measurement circuit

t_{on}, t_{off} test circuit

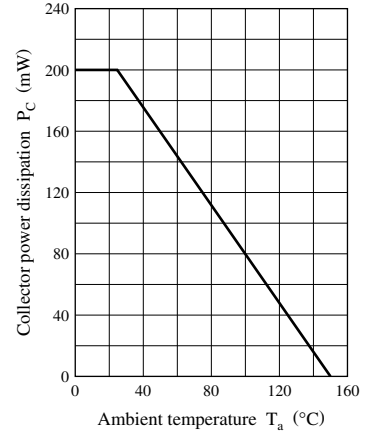


t_{stg} test circuit

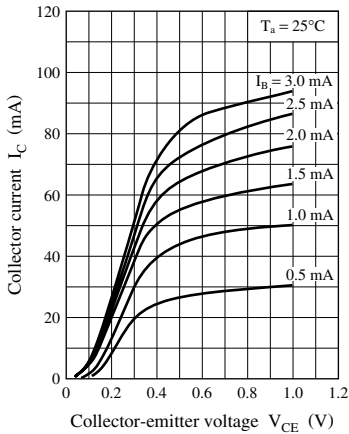


(Waveform at A)

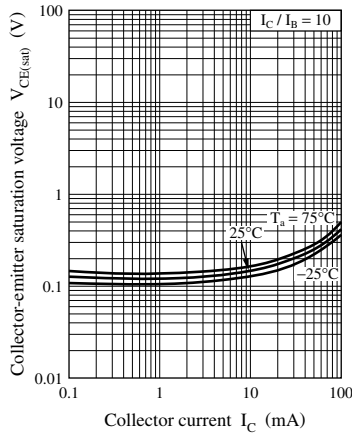
$P_C - T_a$



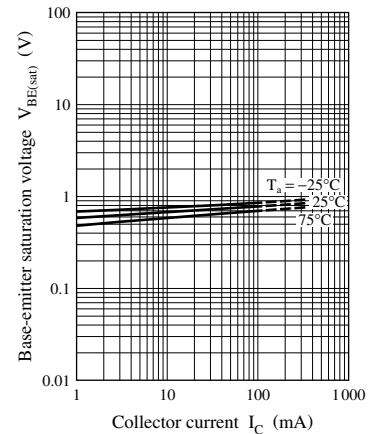
$I_C - V_{CE}$



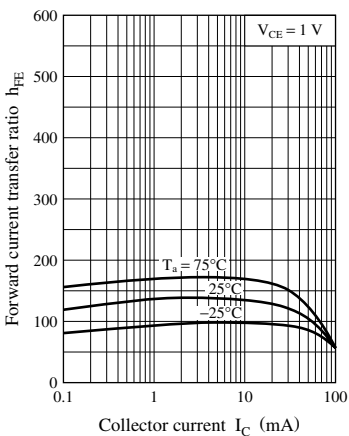
$V_{CE(sat)} - I_C$



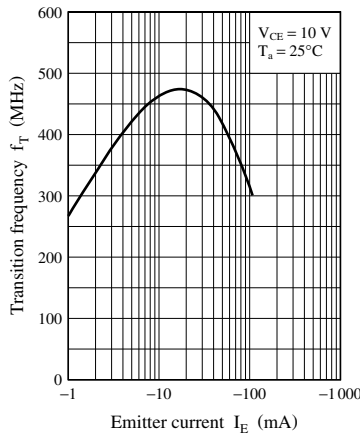
$V_{BE(sat)} - I_C$



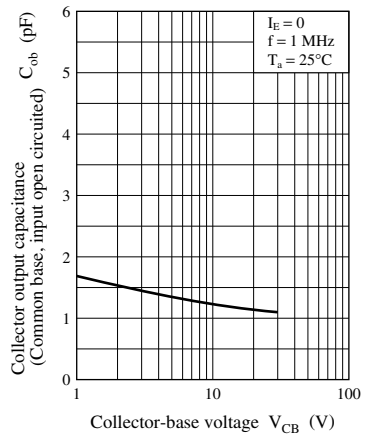
$h_{FE} - I_C$



$f_T - I_E$



$C_{ob} - V_{CB}$



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